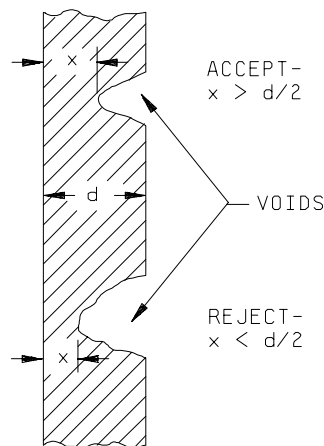


Class HClass K3.2.1.2 Metallization voids.

\*

- a. Void(s) in the metallization, excluding bonding pads, that leaves less than 50 percent of the original metallization width undisturbed (see figure 2032-40h).

- a. Same as Class H.

FIGURE 2032-40h. Class H metallization void criteria.

- b. Void(s) in the bonding pad area that reduces the metallization path width, where it enters the bonding pad, to less than 50 percent of its original metallization width. If two or more metallization paths enter a bonding pad, each shall be considered separately.  
NOTE: Figures 2032-39h and 2032-39k illustrate metallization width reduction at bonding pad criteria for scratches. Void criteria are similar.
- c. Void(s) in the bonding pad area that expose underlying material over more than 25 percent of the original metallization area.  
NOTE: For RF microwave elements on nonconductive substrates, a void created in the bonding pad area as a result of wire bond removal for performance optimization or tuning, is not rejectable provided that the void remains entirely visible.

- b. Less than 75 percent.

- c. Same as class H.